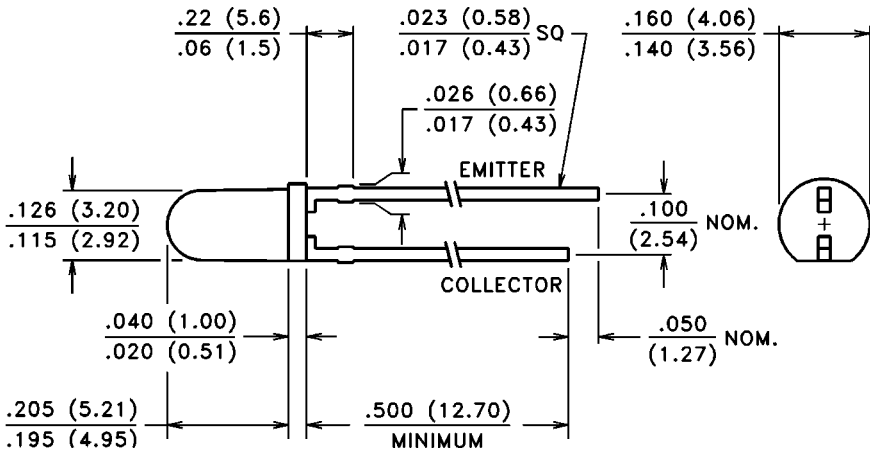
.025" NPN Phototransistors

Clear Long T-1 (3 mm) Plastic Package

VTT3323LA, 4LA, 5LA



PACKAGE DIMENSIONS inch (mm)



CASE 50A LONG T-1 (3 mm)
CHIP TYPE: 25T

PRODUCT DESCRIPTION

A small area high speed NPN silicon phototransistor mounted in a 3 mm diameter, lensed, end looking, transparent plastic package. These devices are spectrally and mechanically matched to the VTE337xLA series of IREDs.

ABSOLUTE MAXIMUM RATINGS ■

(@ 25°C unless otherwise noted)

Maximum Temperatures	
Storage Temperature:	-40°C to 100°C
Operating Temperature:	-40°C to 100°C
Continuous Power Dissipation:	50 mW
Derate above 30°C:	0.71 mW/°C
Maximum Current:	25 mA
Lead Soldering Temperature: (1.6 mm from case, 5 sec. max.)	260°C

ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also typical curves, pages 91-92)

Part Number ■	Light Current			Dark Current		Collector Breakdown	Emitter Breakdown	Saturation Voltage	Rise/Fall Time	Angular Response
	I_C			I_{CEO}		$V_{BR(CEO)}$	$V_{BR(ECO)}$	$V_{CE(SAT)}$	t_R/t_F	$\theta_{1/2}$
	mA		H fc (mW/cm^2) V_{CE} = 5.0 V	H = 0		I_C = 100 µA H = 0	I_E = 100 µA H = 0	I_C = 1.0 mA H = 400 fc	I_C = 1.0 mA R_L = 100 Ω	
	Min.	Max.		(nA) Max.	V_{CE} (Volts)	Volts, Min.	Volts, Min.	Volts, Max.	µsec, Typ.	Typ.
VTT3323LA	2.0	—	20 (1)	100	10	30	5.0	0.25	3.0	±10°
VTT3324LA	4.0	—	20 (1)	100	10	30	5.0	0.25	4.0	±10°
VTT3325LA	6.0	—	20 (1)	100	10	30	5.0	0.25	5.0	±10°

■ Refer to General Product Notes, page 2.